

N-Channel 75-V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|-------------------|---------------------------|-----------------|-------------|
| $V_{(BR)DSS}$ (V) | $r_{DS(on)}$ (Ω) | I_D (A) | Q_g (Typ) |
| 75 | 0.0048 at $V_{GS} = 10$ V | 90 ^d | 105 |
| | 0.006 at $V_{GS} = 8$ V | 90 ^d | |

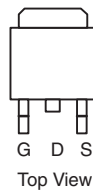
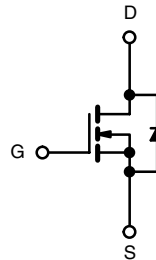
FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- 100 % UIS Tested


RoHS
COMPLIANT

APPLICATIONS

- Power Supply
 - Half-Bridge
 - Secondary Synchronous Rectification
- Industrial

TO-263

Ordering Information: SUM90N08-4m8P-E3 (Lead (Pb)-free)


N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted | | | | |
|--|----------------|----------------------------|------------------|---|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V_{DS} | 75 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current ($T_J = 175$ °C) | I_D | $T_C = 25$ °C | 90 ^d | A |
| | | $T_C = 70$ °C | 90 ^d | |
| Pulsed Drain Current | I_{DM} | 240 | | |
| Avalanche Current | I_{AS} | 70 | | |
| Single Pulse Avalanche Energy ^a | E_{AS} | 245 | mJ | |
| Maximum Power Dissipation ^a | P_D | $T_C = 25$ °C | 300 ^b | W |
| | | $T_A = 25$ °C ^c | 3.75 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 175 | °C | |

| THERMAL RESISTANCE RATINGS | | | |
|--|------------|-------|------|
| Parameter | Symbol | Limit | Unit |
| Junction-to-Ambient (PCB Mount) ^c | R_{thJA} | 40 | °C/W |
| Junction-to-Case (Drain) | R_{thJC} | 0.5 | |

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).
- Package limited.

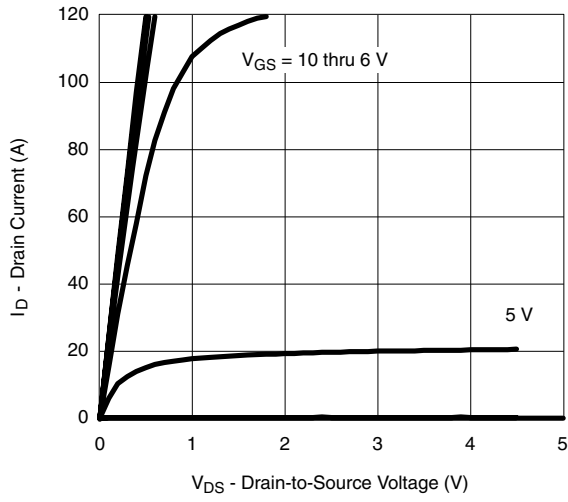
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|---|---------------|--|-----|--------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 75 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2 | | 4 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 250 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | | 50 | |
| | | $V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$ | | | 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$ | 70 | | | A |
| Drain-Source On-State Resistance ^a | $r_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | | 0.004 | 0.0048 | Ω |
| | | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | | 0.0096 | |
| | | $V_{GS} = 8\text{ V}, I_D = 20\text{ A}, T_J = 150\text{ }^\circ\text{C}$ | | | 0.0106 | |
| | | $V_{GS} = 8\text{ V}, I_D = 20\text{ A}$ | | 0.0046 | 0.006 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 20\text{ A}$ | | 58 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$ | | 6460 | | pF |
| Output Capacitance | C_{oss} | | | 571 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 275 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$ | | 105 | 160 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 32 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 28 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | | 1.3 | 2.6 | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 30\text{ V}, R_L = 0.4\text{ }\Omega$ $I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | | 23 | 35 | ns |
| Rise Time ^c | t_r | | | 17 | 26 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 34 | 52 | |
| Fall Time ^c | t_f | | | 8 | 15 | |
| Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$) ^b | | | | | | |
| Continuous Current | I_S | | | | 85 | A |
| Pulsed Current | I_{SM} | | | | 240 | |
| Forward Voltage ^a | V_{SD} | $I_F = 30\text{ A}, V_{GS} = 0\text{ V}$ | | 0.85 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 75\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 68 | 100 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 2.6 | 4 | A |
| Reverse Recovery Charge | Q_{rr} | | | | 88 | 132 |

Notes:

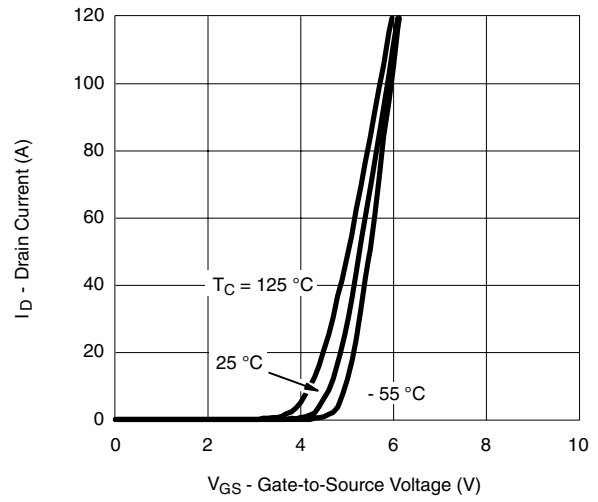
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

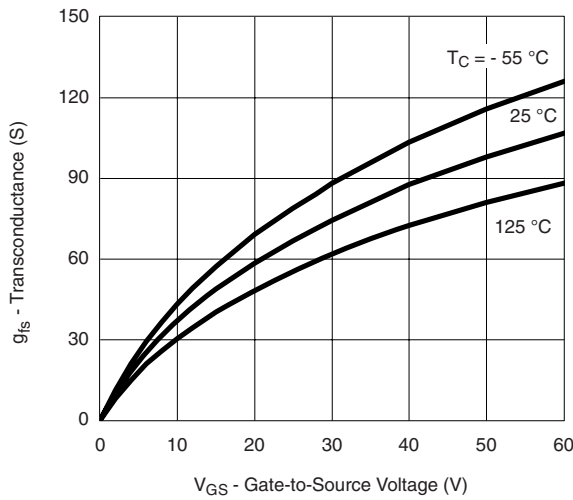
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



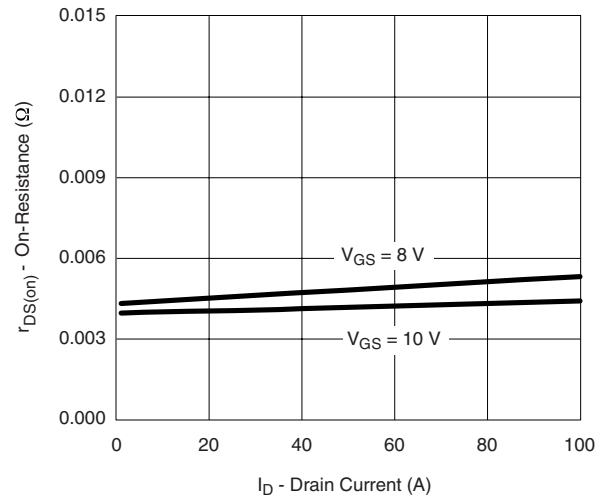
Output Characteristics



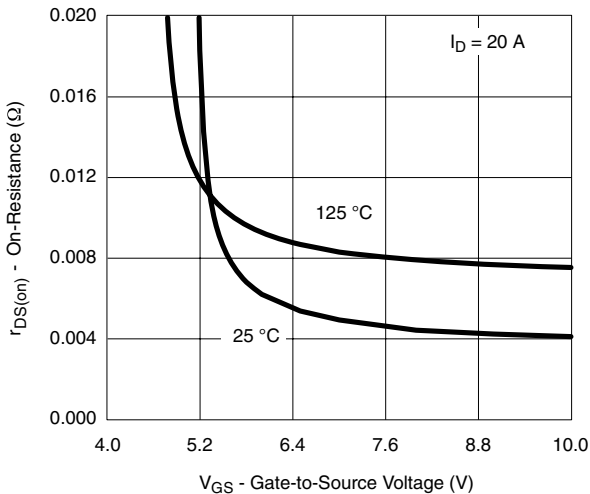
Transfer Characteristics



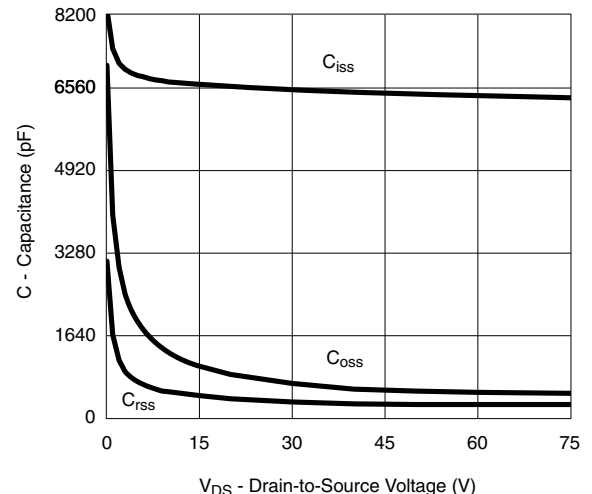
Transconductance



On-Resistance vs. Drain Current

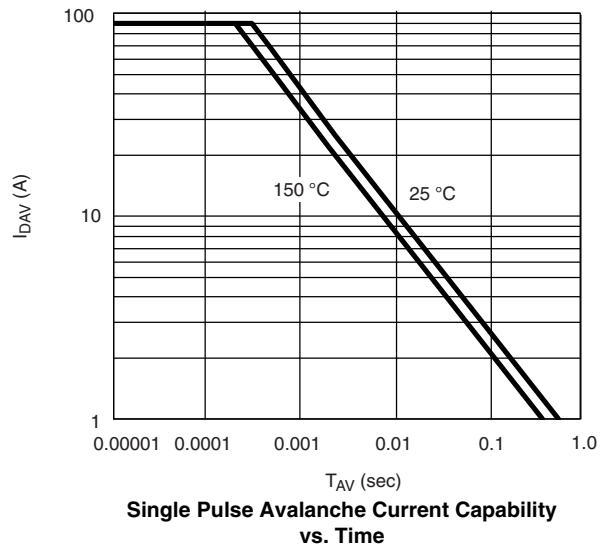
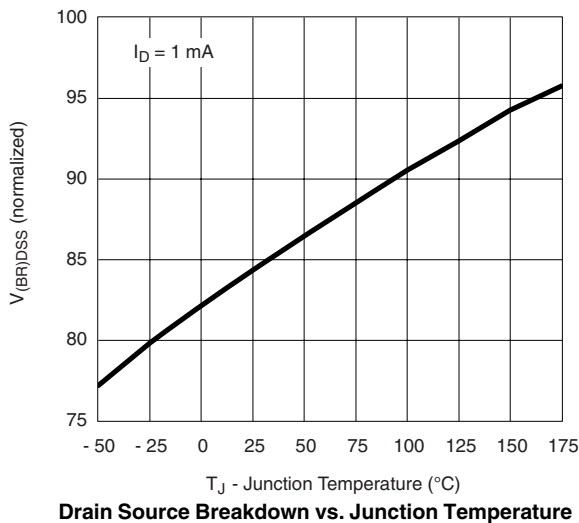
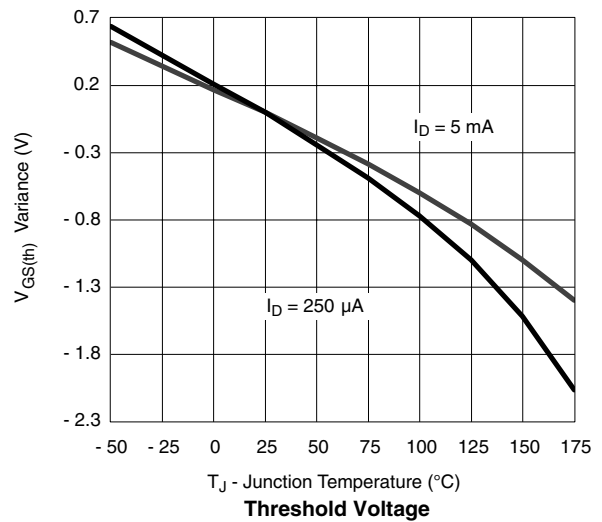
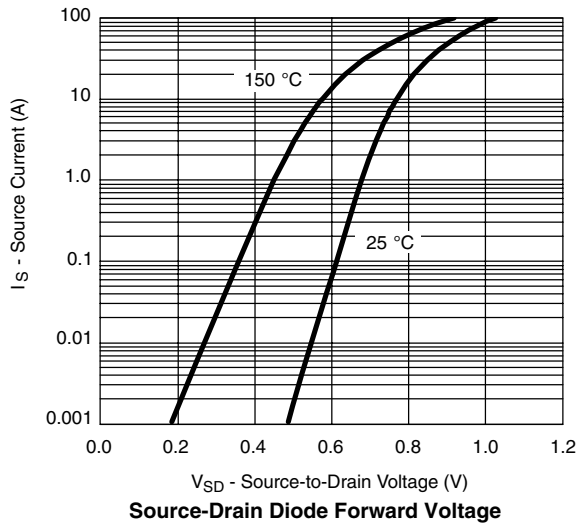
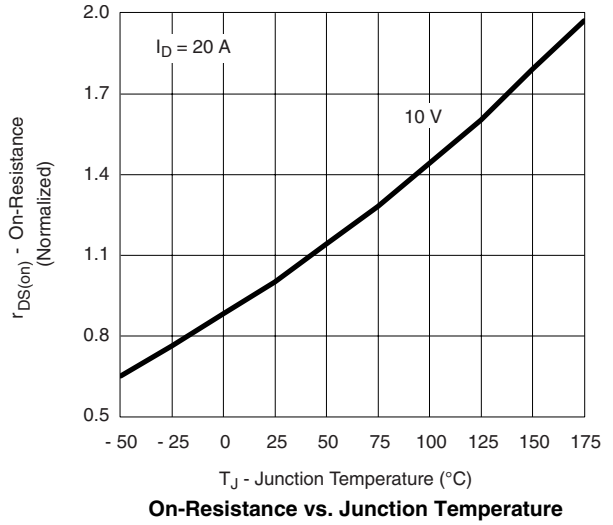
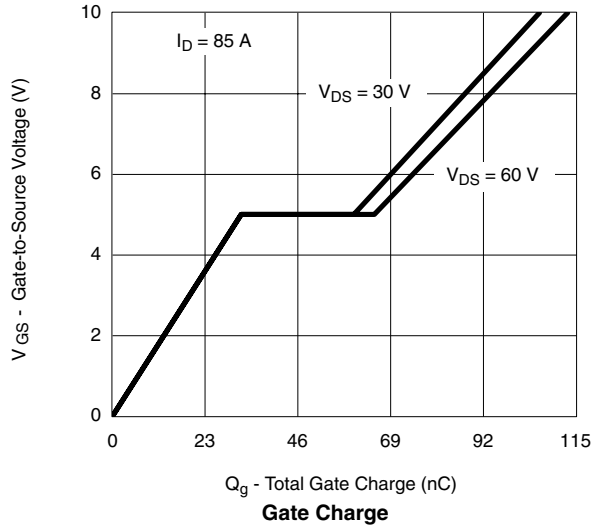


On-resistance vs. Gate-to-Source Voltage

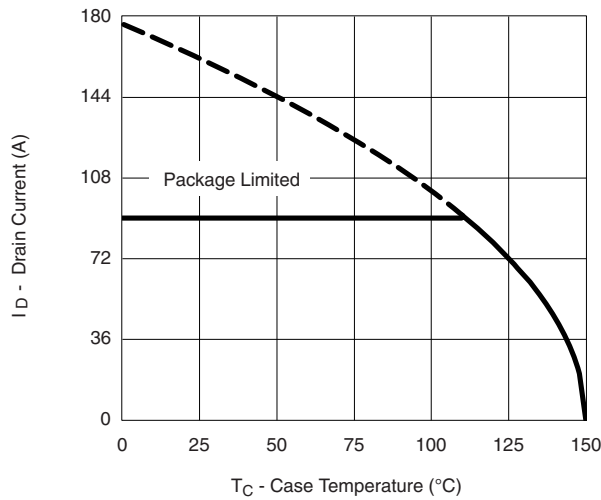


Capacitance

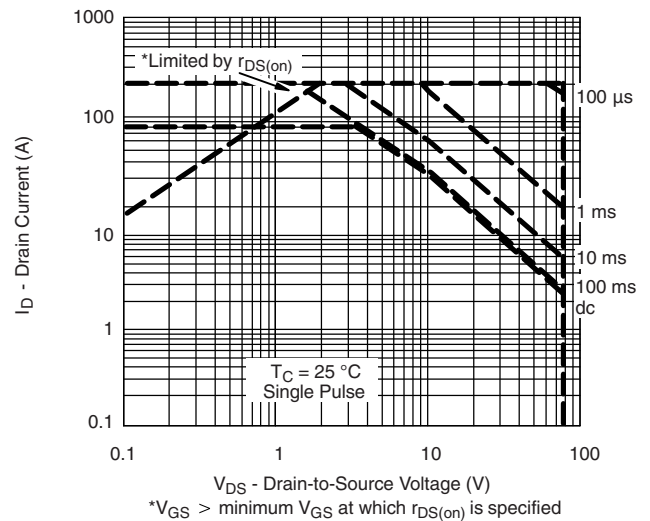
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



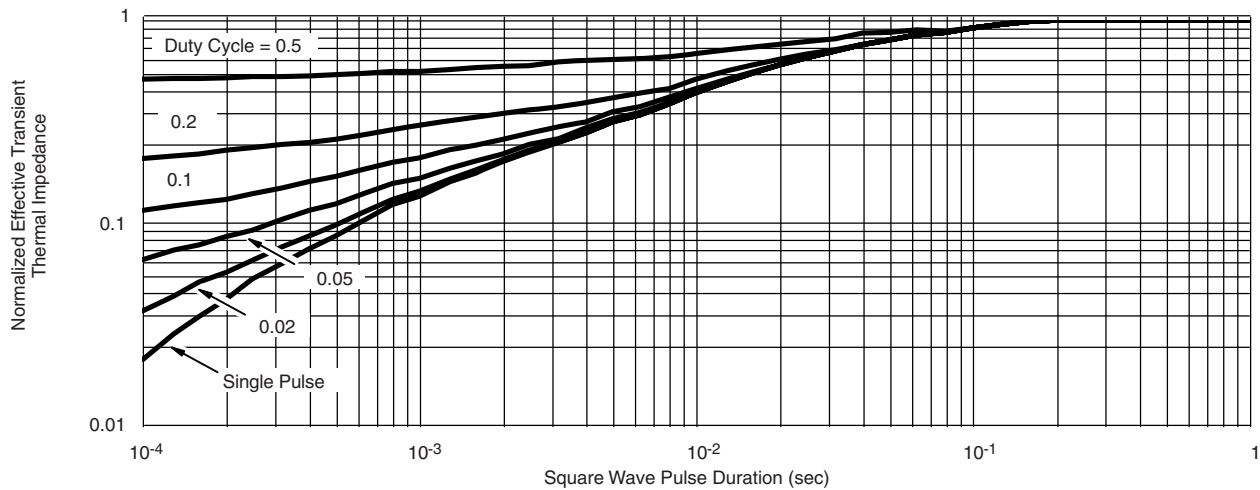
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Maximum Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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